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Si8901EDB
Vishay Siliconix

Bi-Directional P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY

V_{S1S2} (V)	$R_{S1S2(on)}$ (Ω)	I_{S1S2} (A)
- 20	0.060 at $V_{GS} = - 4.5$ V	- 4.4
	0.080 at $V_{GS} = - 2.5$ V	- 3.9
	0.105 at $V_{GS} = - 1.8$ V	- 3.4

FEATURES

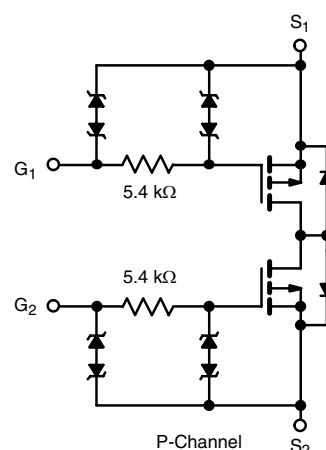
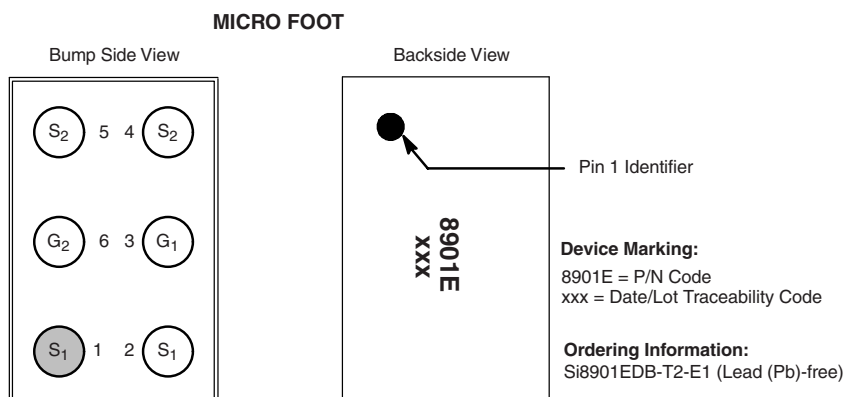
- TrenchFET® Power MOSFET
- Ultra-Low $R_{SS(on)}$
- ESD Protected: 6000 V
- MICRO FOOT® ChipScale Packaging
Reduces Footprint Area, Profile (0.65 mm)
and On-Resistance Per Footprint Area



RoHS
COMPLIANT

APPLICATIONS

- Smart Batteries for Portable Devices



ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$, unless otherwise noted

Parameter		Symbol	5 s	Steady State	Unit
Source1- Source2 Voltage		V_{S1S2}	- 20		V
Gate-Source Voltage		V_{GS}	± 12		
Continuous Source1- Source2 Current ($T_J = 150\text{ }^{\circ}\text{C}$) ^a	$T_A = 25\text{ }^{\circ}\text{C}$	I_{S1S2}	- 4.4	- 3.5	A
	$T_A = 85\text{ }^{\circ}\text{C}$		- 3.2	- 2.5	
Pulsed Source1- Source2 Current		I_{SM}	- 10		
Maximum Power Dissipation ^a	$T_A = 25\text{ }^{\circ}\text{C}$	P_D	1.7	1	W
	$T_A = 85\text{ }^{\circ}\text{C}$		0.8	0.5	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150		$^{\circ}\text{C}$
Package Reflow Conditions ^c	IR/Convection		260		

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	R_{thJA}	$t \leq 5$ s	60	$^\circ\text{C/W}$
		Steady State	95	
Maximum Junction-to-Foot ^b	R_{thJF}	Steady State	18	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. The foot is defined as the top surface of the package.

c. Refer to IPC/JEDEC (J-STD-020C), no manual or hand soldering.

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SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{SS} = V_{GS}, I_D = -350\text{ }\mu\text{A}$	-0.45		-1.0	V
Gate-Body Leakage	I_{GSS}	$V_{SS} = 0\text{ V}, V_{GS} = \pm 4.5\text{ V}$			± 4	μA
		$V_{SS} = 0\text{ V}, V_{GS} = \pm 12\text{ V}$			± 10	mA
Zero Gate Voltage Source Current	I_{S1S2}	$V_{SS} = -20\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
		$V_{SS} = -20\text{ V}, V_{GS} = 0\text{ V}, T_J = 85\text{ }^{\circ}\text{C}$			-5	
On-State Source Current ^a	$I_{S(on)}$	$V_{SS} = -5\text{ V}, V_{GS} = -4.5\text{ V}$	-5			A
Source1- Source2 On-State Resistance ^a	$R_{S1S2(on)}$	$V_{GS} = -4.5\text{ V}, I_{SS} = -1\text{ A}$		0.048	0.060	Ω
		$V_{GS} = -2.5\text{ V}, I_{SS} = -1\text{ A}$		0.062	0.080	
		$V_{GS} = -1.8\text{ V}, I_{SS} = -1\text{ A}$		0.081	0.105	
Forward Transconductance ^a	g_{fs}	$V_{SS} = -10\text{ V}, I_{SS} = -1\text{ A}$		7		S
Dynamic^b						
Turn-On Delay Time	$t_{d(on)}$	$V_{SS} = -10\text{ V}, R_L = 10\text{ }\Omega$ $I_{SS} = -1\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 6\text{ }\Omega$		2.3	3.5	μs
Rise Time	t_r			2.2	3.5	
Turn-Off Delay Time	$t_{d(off)}$			1.3	2	
Fall Time	t_f			9	14	

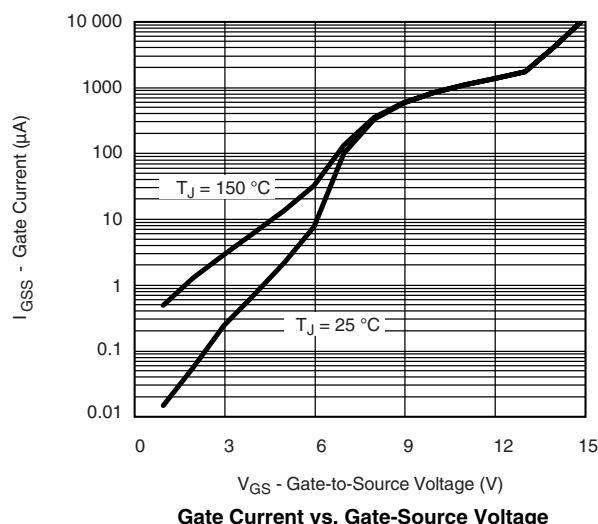
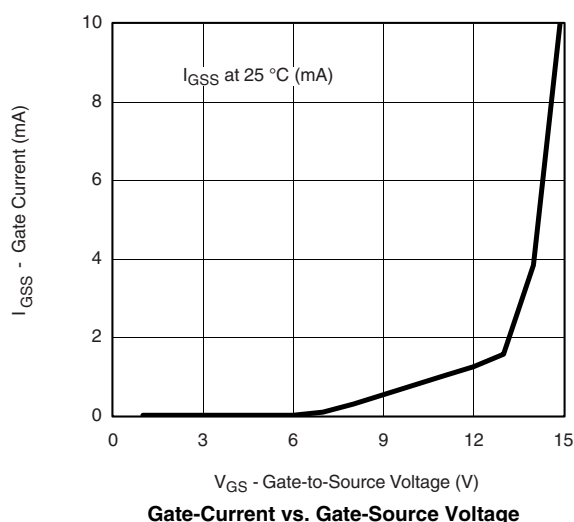
Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS $25\text{ }^{\circ}\text{C}$, unless otherwise noted

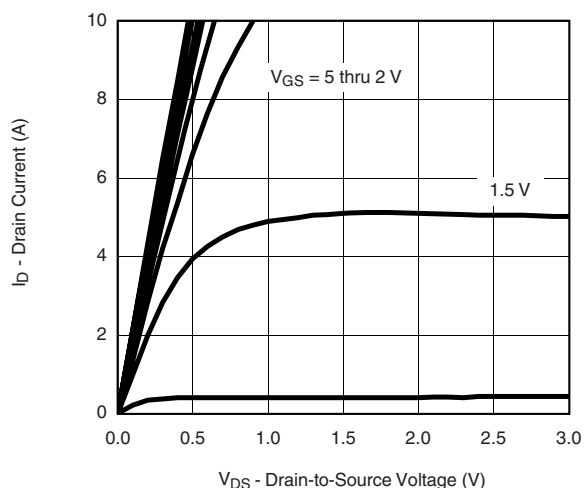




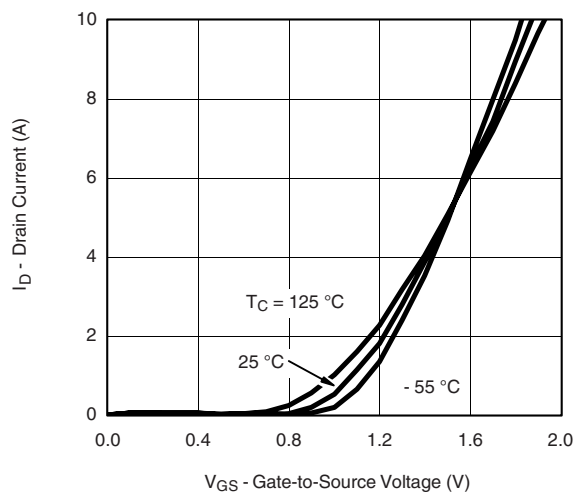
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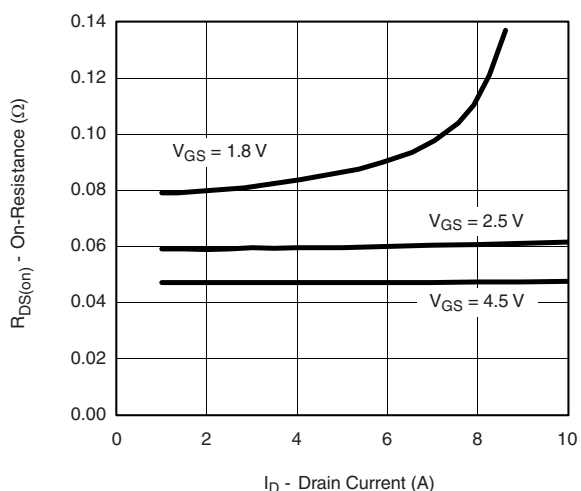
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



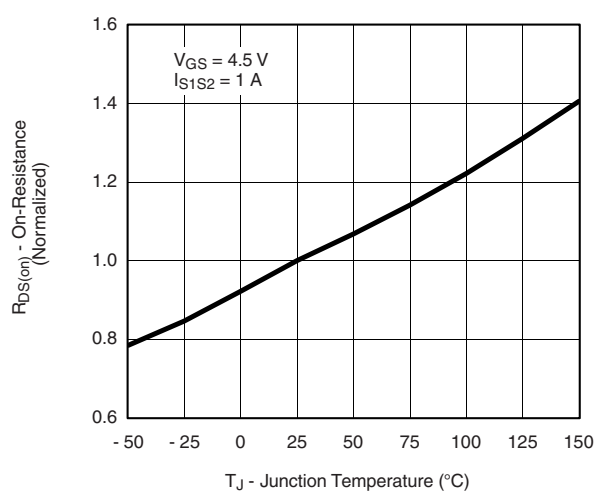
Output Characteristics



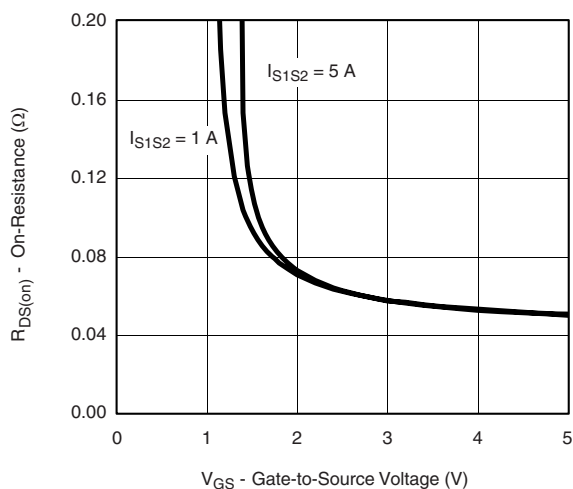
Transfer Characteristics



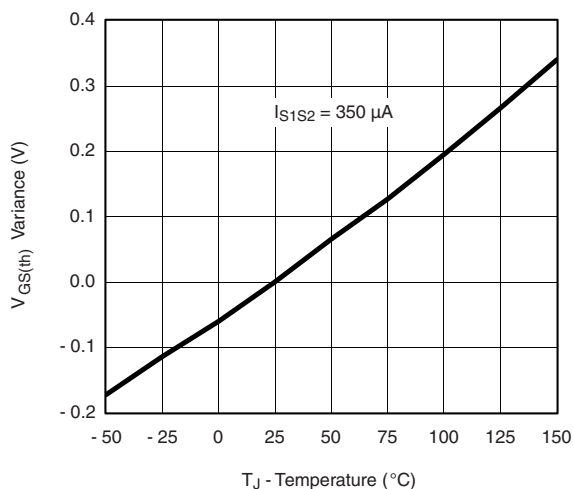
On-Resistance vs. Drain Current



On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage



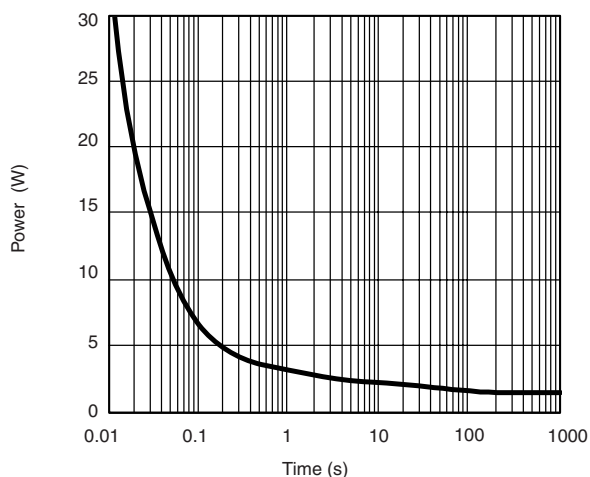
Threshold Voltage

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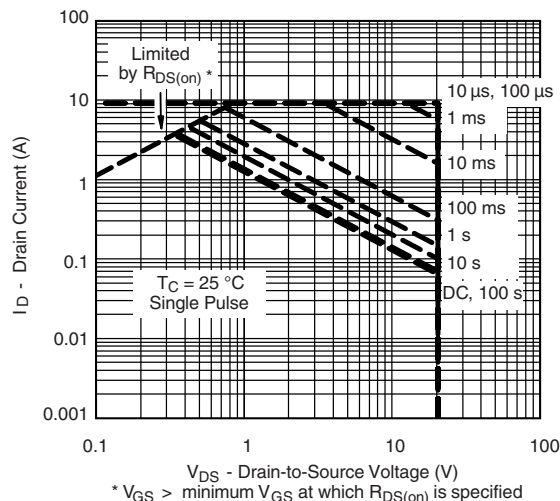
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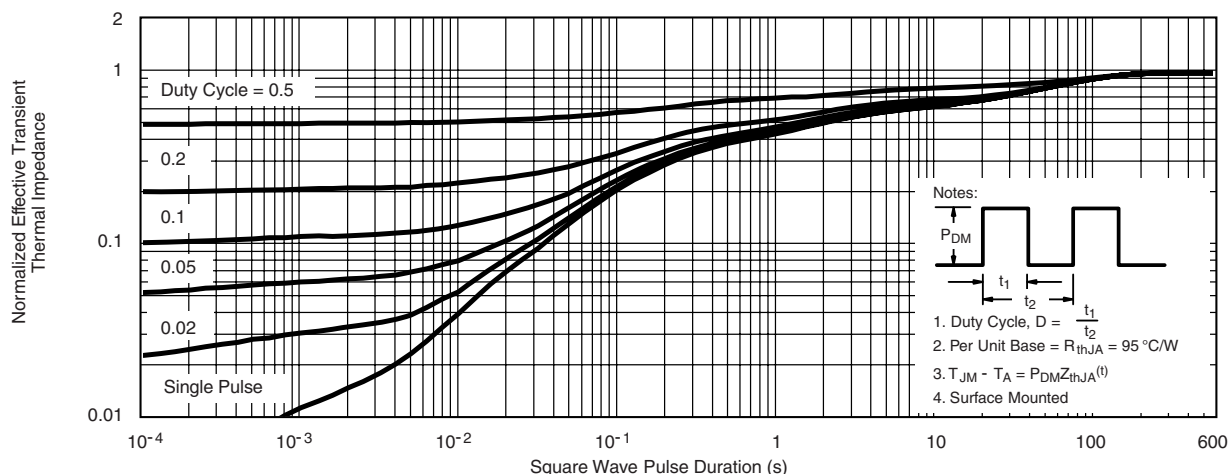
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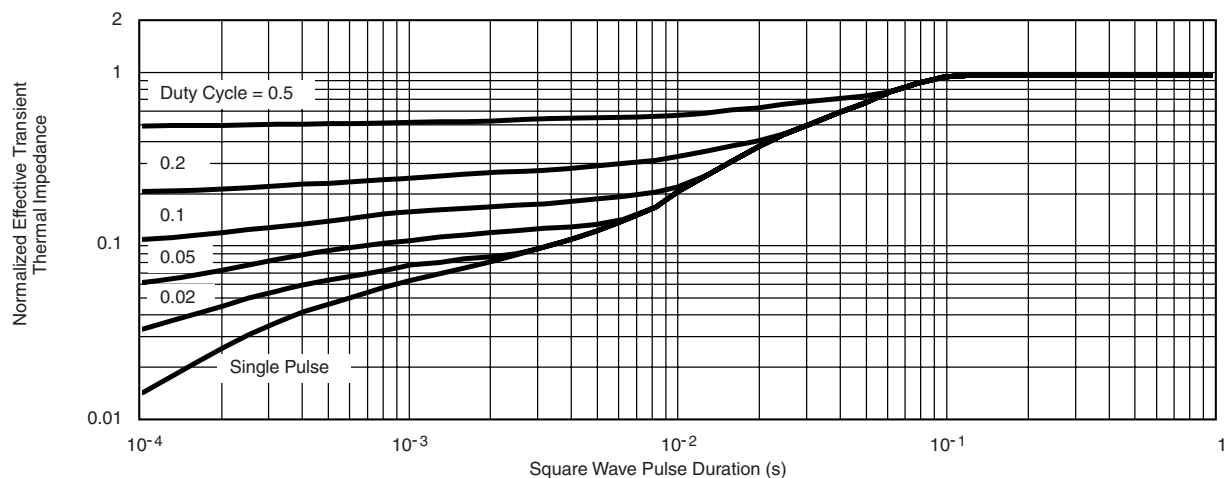
Single Pulse Power, Junction-to-Ambient



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

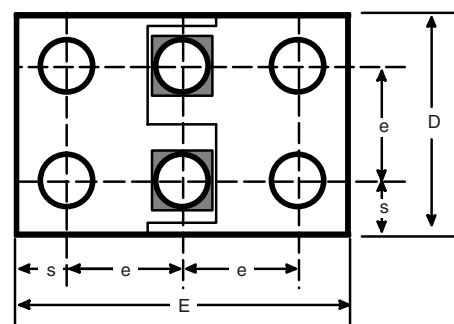
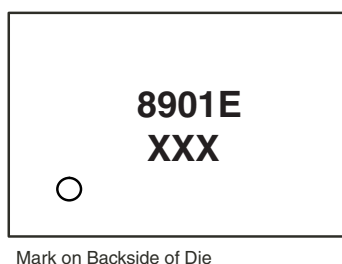
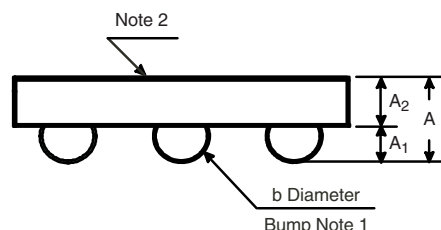
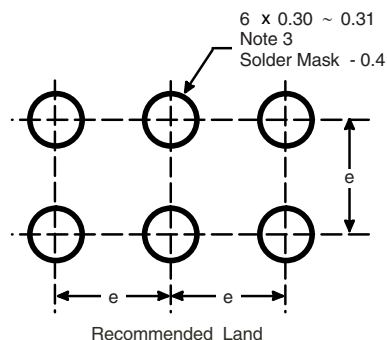


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PACKAGE OUTLINE

MICRO FOOT: 6-BUMP (2 x 3, 0.8 mm PITCH)



Notes (Unless Otherwise Specified):

1. 6 solder bumps are 95.5/3.8/0.7 Sn/Ag/Cu.
2. Backside surface is coated with a Ag/Ni/Ti layer.
3. Non-solder mask defined copper landing pad.
4. Laser marks on the silicon die back.

Dim.	Millimeters ^a		Inches	
	Min.	Max.	Min.	Max.
A	0.600	0.650	0.0236	0.0256
A₁	0.260	0.290	0.102	0.114
A₂	0.340	0.360	0.0134	0.0142
b	0.370	0.410	0.0146	0.0161
D	1.52	1.6	0.0598	0.0630
E	2.32	2.4	0.0913	0.0945
e	0.750	0.850	0.0295	0.0335
s	0.380	0.400	0.0150	0.0157

Notes:

- a. Use millimeters as the primary measurement.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg72941>.



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